

Notice of References Cited	Application/Control No. 10/618,478	Applicant(s)/Patent Under Reexamination KESHNER ET AL.	
	Examiner B. Chen	Art Unit 1762	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2003/0143410 A1	07-2003	Won et al.	428/448
*	B	US-5,834,345 A	11-1998	Shimizu, Kousaku	438/158
*	C	US-6,352,910 B1	03-2002	Harshbarger et al.	438/482
*	D	US-2004/0129212 A1	07-2004	Gadgil et al.	118/715
*	E	US-5,242,530 A	09-1993	Batey et al.	117/90
*	F	US-4,897,282	01-1990	Kniseley et al.	427/446
*	G	US-4,690,830	09-1987	Dickson et al.	438/96
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Watanabe, Takeshi et al., "Microwave-Excited Plasma CVD of a-Si:H Films Utilizing a Hydrogen Plasma Stream or by Direct Excitation of Silane". Japanese Journal of Applied Physics. Vol.26 (1987) pp.1215-1218. Part 1, No.8, 20 August 1987. ABSTRACT ONLY
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.